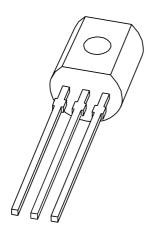
### DISCRETE SEMICONDUCTORS

## DATA SHEET



# BC559 PNP general purpose transistor

Product data sheet Supersedes data of 1999 May 28 2004 Nov 05



### PNP general purpose transistor

**BC559** 

### **FEATURES**

- Low current (max. 100 mA)
- Low voltage (max. 30 V).

### **APPLICATIONS**

• General purpose switching and amplification.

### **DESCRIPTION**

PNP transistor in a TO-92 (SOT54) plastic package. NPN complement: BC549.

### **PINNING**

PIN	DESCRIPTION
1	emitter
2	base
3	collector

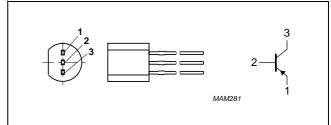


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE					
TIPE NUMBER	NAME	DESCRIPTION	VERSION			
BC559C	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	<b>-</b> 5	V
I <sub>C</sub>	collector current (DC)		_	-100	mA
I <sub>CM</sub>	peak collector current		_	-200	mA
I <sub>BM</sub>	peak base current		_	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

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### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	250	K/W

### Note

1. Transistor mounted on an FR4 printed-circuit board.

### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

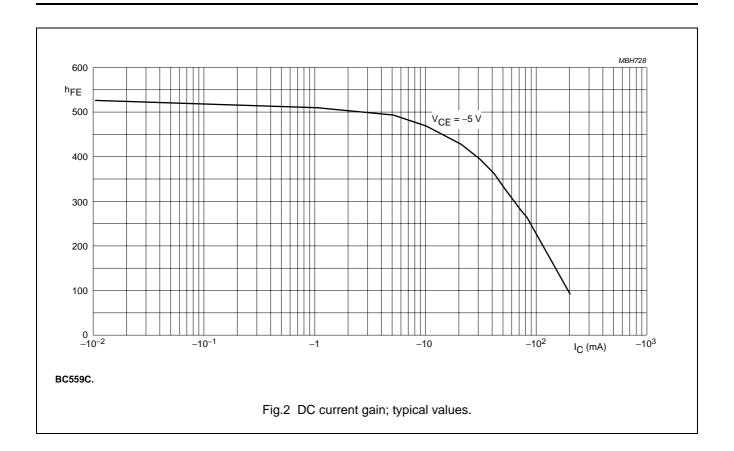
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	_	-1	-15	nA
		$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	_	-	-4	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain; BC559C	$V_{CE} = -5 \text{ V}$ ; $I_C = -2 \text{ mA}$ ; see Fig.2	420	-	800	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-60	-300	mV
	voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}$	_	-180	-650	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -10 \text{ mA}$ ; $I_B = -0.5 \text{ mA}$ ; note 1	_	-750	_	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$	_	-930	_	mV
V <sub>BE</sub>	base-emitter voltage	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}; \text{ note } 2$	-600	-650	-750	mV
		$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA; note } 2$	_	_	-820	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	_	4	_	pF
f <sub>T</sub>	transition frequency	$V_{CB} = -5 \text{ V}; I_E = -10 \text{ mA}; f = 100 \text{ MHz}$	100	_	_	MHz
F	noise figure; BC559C	$V_{CE} = -5 \text{ V}; I_C = -200  \mu\text{A}; R_S = 2  k\Omega;$	_	_	4	dB
		f = 30 Hz to 15.7 kHz				
		$V_{CE} = -5 \text{ V; } I_{C} = -200  \mu\text{A; } R_{S} = 2  k\Omega;$ $f = 1 \text{ kHz; } B = 200 \text{ Hz}$		_	4	dB

### **Notes**

- 1.  $V_{BEsat}$  decreases by about  $-1.7 \ mV/K$  with increasing temperature.
- 2.  $V_{BE}$  decreases by about -2 mV/K with increasing temperature.

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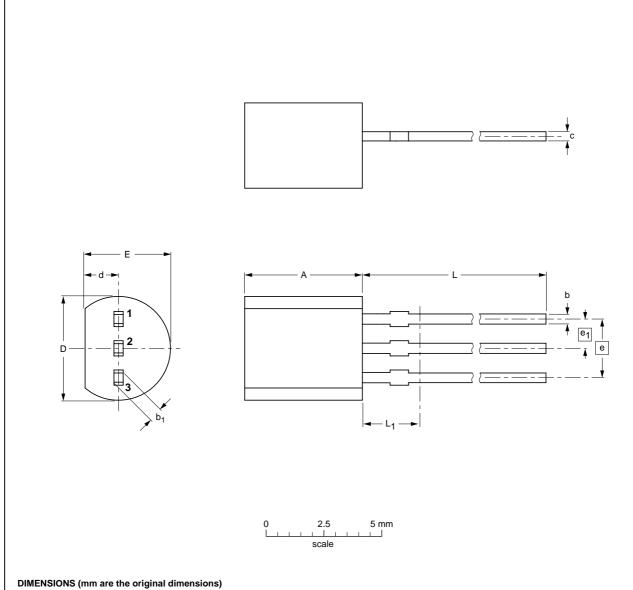
### PNP general purpose transistor

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### **PACKAGE OUTLINE**

### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A			<del>-04-06-28-</del> 04-11-16	

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### PNP general purpose transistor

BC559

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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### **Contact information**

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